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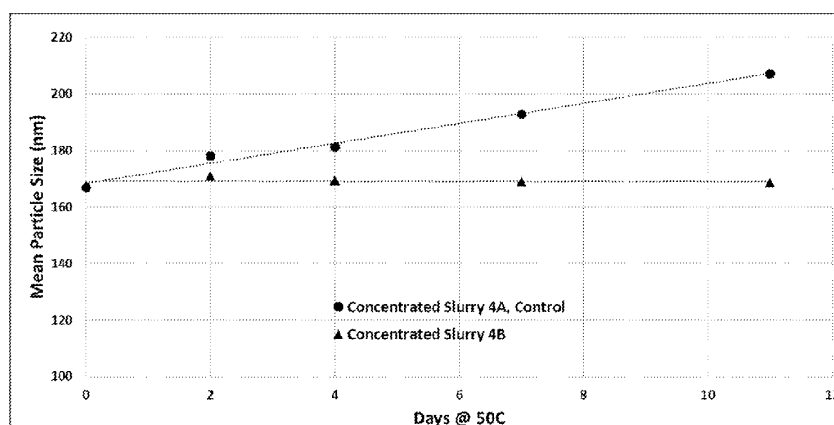
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GQ, GW, KM, ML, MR, NE, SN, TD, TG).(54) Title: STABLE CHEMICAL MECHANICAL PLANARIZATION POLISHING COMPOSITIONS AND METHODS FOR  
HIGH RATE SILICON OXIDE REMOVAL

FIGURE 1

(57) Abstract: The present Chemical Mechanical Planarization (CMP) polishing compositions, methods, and systems have low conductivity, high stability, and offer high removal rates of silicon dioxide for achieving a topographically corrected wafer surface with low defects. The CMP polishing compositions use a unique combination of silica particles, and an amino acid having at least one carboxyl group, preferably at least one amino group -NH<sub>2</sub>, and preferably at least one imidazole group, and a silicate.

[Continued on next page]

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